

T-01-09

GENERAL PURPOSE HIGH CONDUCTANCE DIODES

1N461A
1N462A
1N463A

ABSOLUTE MAXIMUM RATINGS

- V_F 1.0 V @ 100 mA
- I_R 500 nA @ WIV

Temperatures

Storage Temperature Range	-65 °C to +200 °C
Maximum Junction Operating Temperature	+175 °C
Lead Temperature	+260 °C

Power Dissipation

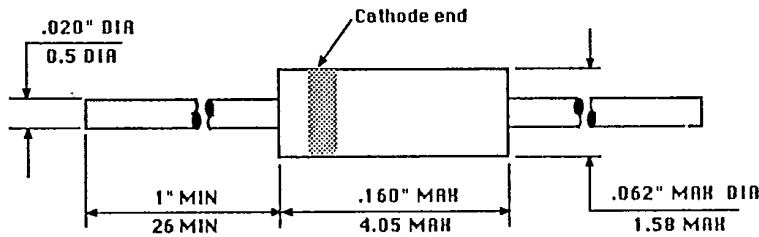
Maximum Total Power Dissipation at 25 °C Ambient	500 mW
Linear Power Derating Factor (from 25 °C)	3.33 mW/°C

Maximum Voltage and Currents

	1N461A	1N462A	1N463A	1N464A
WIV Working Inverse Voltage	25V	60V	175V	125V
I_O Average Rectified Current	200 mA	200 mA	200 mA	200mA
I_F Continuous Forward Current	500mA	500mA	500mA	500mA
i_F Peak Repetitive Forward Current	600mA	600mA	600mA	600mA
i_F (surge) Peak Forward Surge Current				
Pulse Width = 1μs	4.0 A	4.0 A	4.0 A	4.0 A
Pulse Width = 1s	1.0A	1.0A	1.0A	1.0A

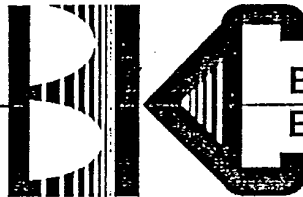
ELECTRICAL CHARACTERISTICS (25 °C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
V_F	Forward Voltage		1.0	V	$I_F = 100$ mA
I_R	Reverse Current		500	nA	$V_R =$ Rated WIV
			30	μA	$V_R =$ Rated WIV, $T_A = 150$ °C
B_V	Breakdown Voltage				
	1N461A	30		V	$I_R = 100$ μA
	1N462A	70		V	$I_R = 100$ μA
	1N463A	200		V	$I_R = 100$ μA
	1N464A	150		V	$I_R = 100$ μA



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